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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/954,864	09/17/2001	Satyadev R. Patel	P68-US	8736
26148	7590	08/18/2005	EXAMINER	
REFLECTIVITY, INC. 350 POTRERO AVENUE SUNNYVALE, CA 94085			OLSEN, ALLAN W	
			ART UNIT	PAPER NUMBER

1763

DATE MAILED: 08/18/2005

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Serial No. : 09954864  
Applicant : Satyadev R. Patel  
Filing Date : September 17, 2001  
Date Mailed : August 18, 2005

## ACKNOWLEDGEMENT OF REQUEST

### *Notice of Allowance/Allowability Mailed*

The request for a copy of the initialed PTO 1449, dated March 25, 2005, has been received by the U.S. Patent and Trademark Office.

- Requested copy attached

Natarsha Horne  
For the Office of Patent Publication



PTO/SB/06A (10-01)  
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Substitute for form 1449A/PTO			<b>Complete if Known</b>		
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)			Application Number	09/854,884	
			Filing Date	9/17/01	
			First Named Inventor	Patel	
			Art Unit	1783	
			Examiner Name	Clsen, Allan	
Sheet	1	of	6	Attorney Docket Number	P68-US

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No. <sup>1</sup>	Document Number Number - Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
None		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,190,488	02-26-1980	Winters, H.P.	
		US- 4,310,380	12-12-1982	Flamm et al.	
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		US- 6,436,229	08-20-2002	Tal et al.	
		US- 6,162,367	12-19-2000	Tal et al.	
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		US- 6,355,181 B1	03-12-2002	McQuarrie, A.O.	
		US- 2001/0002693 A1	08-07-2001	Tal et al.	
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		US- 2002/0183699	12-12-2002	Raid	
		US- 2002/0121502 A1	06-15-2002	Patel, et al.	
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		US- 2002/0047172 A1	04-25-2002	Raid	
	Also	US- 2003/0168342 A1	09/04/03	Chinn, et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
None		EP-0704884-A2	04-03-1998	Makita, J.		
		EP-0822582-A2	02-04-1998	Bhardwaj, J.K.		
		EP-0822584-A2	04-04-1998	Bhardwaj, J.K.		
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		JP-1983/60057938-A	04-03-1983	Katsumi et al.		
	Also		WO-98/32163	07-23-1998	Tai et al.	

Examiner Signature	<i>Allan Olsen</i>	Date Considered	3/7/05
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		Application Number	09/854,864
		Filing Date	9/17/01
		First Named Inventor	Patel
		Art Unit	1763
Examiner Name	Olsen, Allan		
Attorney Docket Number	P68-US		
Sheet	2	of	8

U.S. PATENT DOCUMENTS					
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		Number - Kind Code 2 (if known)			
A.C.O.		US- 6,409,876 B1	08-25-2002	McQuarrie, et al.	
		US- 6,398,619 B1	05-28-2002	Hubers, et al.	
		US- 6,578,489 B2	06/10/03	Leung, et al.	
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		US- 6,115,172	09-05-2000	Jeong	
		US- 6,204,080	03-20-2001	Hwang	
		US- 2003/0071015 A1	04/17/03	Chinn, et al.	
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FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>4</sup> - Number <sup>2</sup> - Kind Code <sup>5</sup> (if known)				
A.C.O.		JP-1997/09251991-A	09-22-1997	Kazushi et al.		
		JP-1998/10313128-A	11-24-1998	Hanmin et al.		
		JP-1998/10317169-A	12-02-1998	McQuarrie et al.		
		JP-1998/61187238-A	08-20-1998	Nobuo et al.		
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		JP-1998/63155713-A	06-28-1998	Tadashi, F.		
		JP-1998/61053732-A	03-17-1998	Arata et al.		
		JP-1998/61134019-A	06-21-1998	Shinji et al.		
		JP-1998/61181131-A	08-13-1998	Shinji et al.		

Examiner Signature	<i>Allan Olsen</i>	Date Considered	3-7-05
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		Filing Date	9/17/01
		First Named Inventor	Patel
		Group Art Unit	1763
		Examiner Name	Olsen, Allan
		Attorney Docket Number	P68-US
Sheet	4	of	8

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
Auo		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F <sub>2</sub> and XeF <sub>2</sub> Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
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		HABUKA et al., "Dominant Overall Chemical Reaction in a Chlorine Trifluoride-Silicon-Nitrogen System at Atmospheric Pressure", Japan Journal of Applied Physics Vol. 38 (1999), pp. 6466-6469.	
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Examiner Signature	Allan Olsen	Date Considered	3-7-05
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		Filing Date	9/17/01
		First Named Inventor	Patel
		Group Art Unit	1763
		Examiner Name	Olsen, Allan
Sheet 5 of 6	Attorney Docket Number	P68-US	

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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See		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-776, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
		WINTERS et al., "The Etching of Silicon with XeF <sub>2</sub> Vapor", Appl. Phys. Letter, Vol. 34(1) (January 1, 1979), pp. 70-73.	
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		CHANG et al., "Gas-Phase Silicon Micromachining with Silicon Difluoride", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).	

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Auo		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/KaF2 Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
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		SEBEL et al., "Etching of Si Through a Thick Condensed XeF2 Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 5 (Sept/Oct 2000), pp. 2090-2097 (abstract only).	

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